

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
40V	1.6mΩ@10V	120A

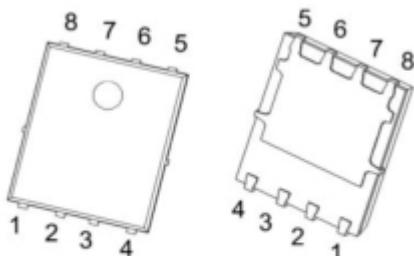
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

Application

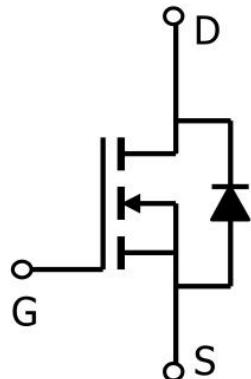
- DC-DC Converter
- Ideal for high-frequency switching and synchronous rectification

Package

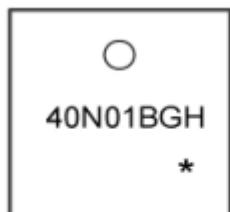


PDFNWB5X6-8L

Circuit diagram



Marking



40N01BGH =Device Code
 * =Month Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹ ($T_c=25^\circ\text{C}$)	I_D	120	A
Pulsed Drain Current ²	I_{DM}	520	A
Single Pulse Avalanche Energy ³	E_{AS}	529	mJ
Total Power Dissipation ⁴ ($T_c=25^\circ\text{C}$)	P_D	120	W
Thermal Resistance Junction-Case ¹	R_{eJC}	1.04	$^\circ\text{C}/\text{W}$
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ\text{C}$

Electrical characteristics

($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	40			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 32\text{V}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	μA
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2	3	4	V
Static Drain-Source On-Resistance ²	$R_{DS(\text{on})}$	$V_{GS} = 10\text{V}, I_D = 30\text{A}$		1.6	2.5	$\text{m}\Omega$
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		3485		pF
Output Capacitance	C_{oss}			1208		
Reverse Transfer Capacitance	C_{rss}			59		
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 20\text{V}, V_{GS} = 10\text{V}, I_D = 65\text{A}$		57		pF
Gate-Source Charge	Q_{gs}			9.5		
Gate-Drain Charge	Q_{gd}			11		
Turn-On Delay Time	$T_{d(on)}$	$V_{DD} = 20\text{V}, V_{GS} = 10\text{V}, R_G = 1.6\Omega, I_D = 65\text{A}$		10		nS
Rise Time	T_r			3		
Turn-Off Delay Time	$T_{d(off)}$			35		
Fall Time	T_f			4		
Diode Characteristics						
Diode Forward Voltage ²	V_{SD}	$V_{GS} = 0\text{V}, I_S = 20\text{A}, T_J = 25^\circ\text{C}$			1.2	V

Note:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{DD}=15\text{V}, V_{GS}=10\text{V}, L=0.5\text{mH}, R_G=25\Omega$

Typical Characteristics

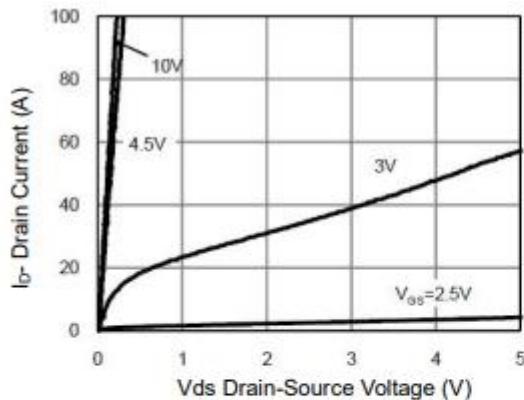


Figure 1 Output Characteristics

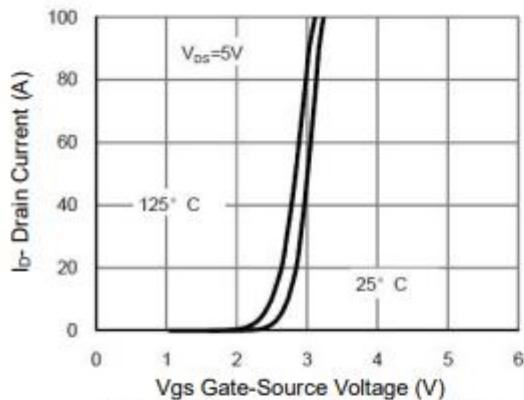


Figure 2 Transfer Characteristics

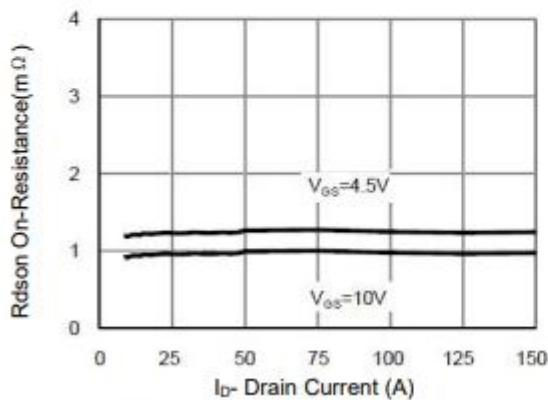


Figure 3 Rdson- Drain Current

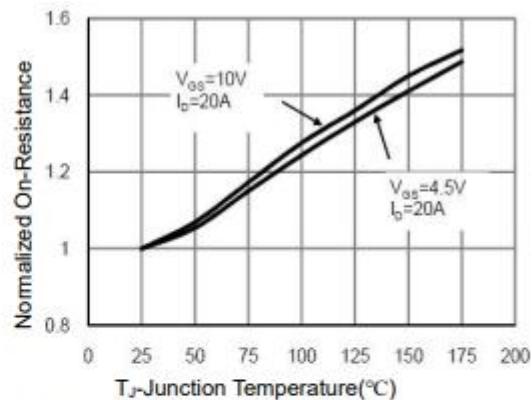


Figure 4 Rdson-Junction Temperature

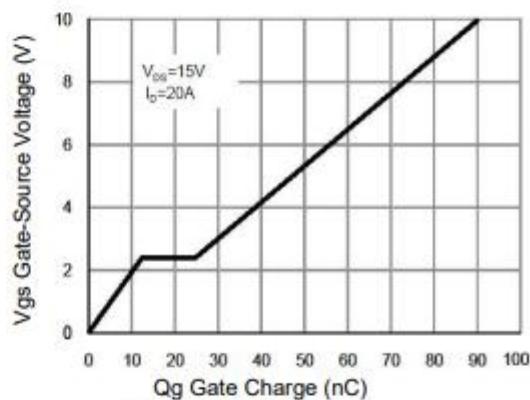


Figure 5 Gate Charge

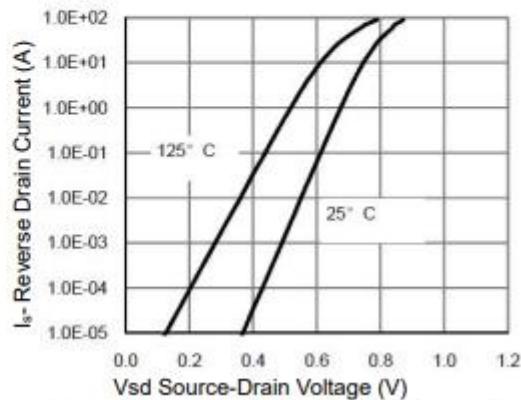


Figure 6 Source- Drift Diode Forward

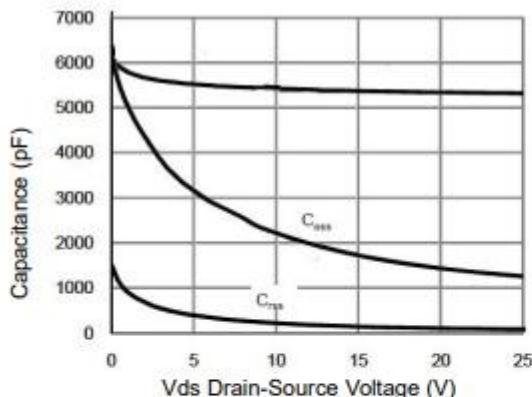


Figure 7 Capacitance vs Vds

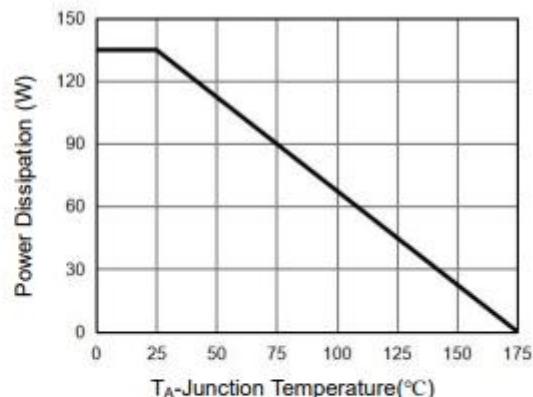


Figure 9 Power De-rating

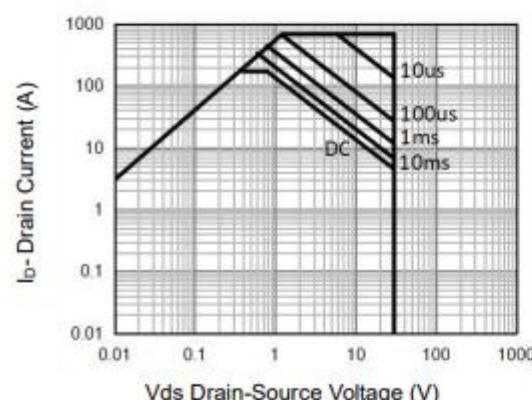


Figure 8 Safe Operation Area (Note3)

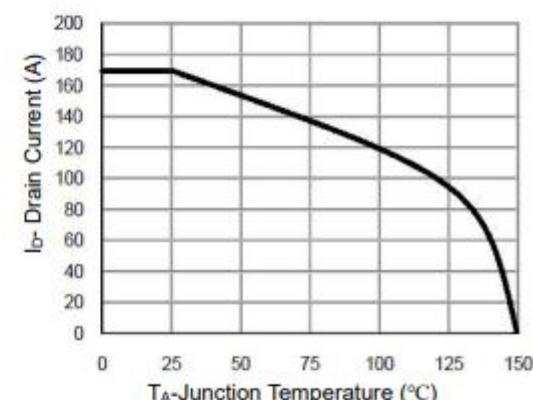


Figure 10 Current De-rating

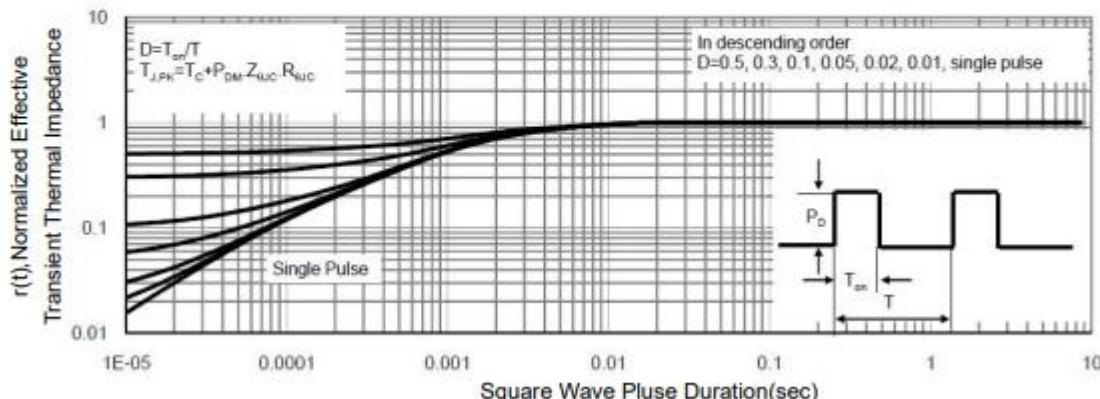
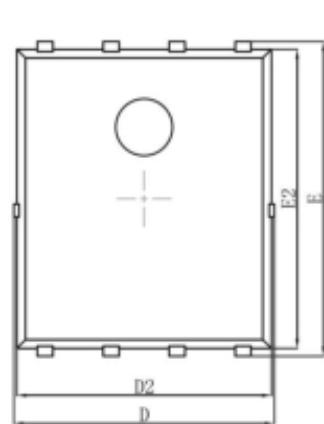
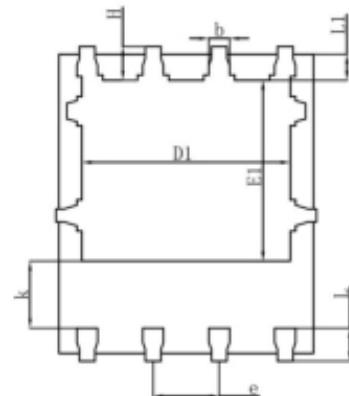


Figure 11 Normalized Maximum Transient Thermal Impedance

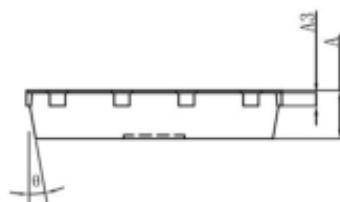
PDFNWB5X6-8L Package Information



Top View
[顶视图]



Bottom View
[底视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°		12°	